

RELIABILITY REPORT
FOR
MAX3203EExT
PLASTIC ENCAPSULATED/CHIP SCALE DEVICES

August 3, 2003

MAXIM INTEGRATED PRODUCTS

120 SAN GABRIEL DR.

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Conclusion

The MAX3203E successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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I. Device Description

A. General

The MAX3203E is a low-capacitance $\pm 15\text{kV}$ ESD-protection diode array designed to protect sensitive electronics attached to communication lines. Each channel consists of a pair of diodes that steer ESD current pulses to V_{CC} or GND. The MAX3203E protect against ESD pulses up to $\pm 15\text{kV}$ Human Body Model, $\pm 8\text{kV}$ Contact Discharge, and $\pm 15\text{kV}$ Air-Gap Discharge, as specified in IEC 61000-4-2. This device has 5pF capacitance per channel, making it ideal for use on high-speed data I/O interfaces.

The MAX3203E is a triple-ESD structure intended for USB On-the-Go (OTG) and video applications.

The device is available in tiny chip-scale (UCSP™) and thin QFN package, and is specified for -40°C to $+85^{\circ}\text{C}$ operation.

B. Absolute Maximum Ratings

| <u>Item</u> | <u>Rating</u> |
|--|---|
| VCC to GND | -0.3V to +7.0V |
| I/O_ to GND | -0.3V to (VCC + 0.3V) |
| Operating Temperature Range | -40°C to $+85^{\circ}\text{C}$ |
| Storage Temperature Range | -65°C to $+150^{\circ}\text{C}$ |
| Junction Temperature | $+150^{\circ}\text{C}$ |
| Bump Temperature (soldering) (Note 1) | |
| Infrared (15s) | $+220^{\circ}\text{C}$ |
| Vapor Phase (60s) | $+215^{\circ}\text{C}$ |
| Lead Temperature (soldering, 10s) | $+300^{\circ}\text{C}$ |
| Continuous Power Dissipation (TA = $+70^{\circ}\text{C}$) | |
| 6-PIN Thin QFN (3 x 3) | 1951mW |
| 3 x 2 UCSP | 273mW |
| Derates above $+70^{\circ}\text{C}$ | |
| 6-PIN Thin QFN (3 x 3) | $24.4\text{mW}/^{\circ}\text{C}$ |
| 3 x 2 UCSP | $3.4\text{mW}/^{\circ}\text{C}$ |

Note 1: The UCSP devices are constructed using a unique set of packaging techniques that impose a limit on the thermal profile the device can be exposed to during board-level solder attach and rework. This limit permits the use of only the solder profiles recommended in the industry-standard specification, JEDEC 020A, paragraph 7.6, Table 3 for IR/VPF and Convection Reflow. Preheating is required. Hand or wave soldering is not allowed.

II. Manufacturing Information

| | |
|----------------------------------|--|
| A. Description/Function: | Low-Capacitance, 2/3/4/6-Channel, $\pm 15\text{kV}$ ESD Protection Arrays for High-Speed Data Interfaces |
| B. Process: | BCD80 |
| C. Number of Device Transistors: | 6 |
| D. Fabrication Location: | Oregon, USA |
| E. Assembly Location: | Philippines or Thailand |
| F. Date of Initial Production: | April, 2003 |

III. Packaging Information

| | | |
|--|--------------------------|--------------------|
| A. Package Type: | 6-Pin QFN (3 x 3) | 6-Bump UCSP |
| B. Lead Frame: | Copper | N/A |
| C. Lead Finish: | Solder Plate | N/A |
| D. Die Attach: | Silver-filled Epoxy | N/A |
| E. Bondwire: | Gold (1 mil dia.) | N/A |
| F. Mold Material: | Epoxy with silica filler | N/A |
| G. Assembly Diagram: | # 05-9000-0264 | # 05-9000-0262 |
| H. Flammability Rating: | Class UL94-V0 | Class UL94-V0 |
| I. Classification of Moisture Sensitivity per JEDEC standard JESD22-112: | Level 1 | Level 1 |

IV. Die Information

| | |
|----------------------------|---|
| A. Dimensions: | 44 X 64 mils |
| B. Passivation: | $\text{Si}_3\text{N}_4/\text{SiO}_2$ (Silicon nitride/ Silicon dioxide) |
| C. Interconnect: | Aluminum/Si (Si = 1%) |
| D. Backside Metallization: | None |
| E. Minimum Metal Width: | 3 microns (as drawn) |
| F. Minimum Metal Spacing: | 3 microns (as drawn) |
| G. Bondpad Dimensions: | 5 mil. Sq. |
| H. Isolation Dielectric: | SiO_2 |
| I. Die Separation Method: | Wafer Saw |

V. Quality Assurance Information

- A. Quality Assurance Contacts: Jim Pedicord (Manager, Reliability Operations)
Bryan Preeshl (Executive Director of QA)
Kenneth Huening (Vice President)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in **Table 1**. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4389 \times 48 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

↑
Temperature Acceleration factor assuming an activation energy of 0.8eV

$$\lambda = 22.62 \times 10^{-9}$$

$$\lambda = 22.62 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

This low failure rate represents data collected from Maxim's reliability monitor program. In addition to routine production Burn-In, Maxim pulls a sample from every fabrication process three times per week and subjects it to an extended Burn-In prior to shipment to ensure its reliability. The reliability control level for each lot to be shipped as standard product is 59 F.I.T. at a 60% confidence level, which equates to 3 failures in an 80 piece sample. Maxim performs failure analysis on any lot that exceeds this reliability control level. Attached Burn-In Schematic (Spec. # 06-6090) shows the static Burn-In circuit. Maxim also performs quarterly 1000 hour life test monitors. This data is published in the Product Reliability Report (**RR-1M**).

B. Moisture Resistance Tests

Maxim pulls pressure pot samples from every assembly process three times per week. Each lot sample must meet an LTPD = 20 or less before shipment as standard product. Additionally, the industry standard 85°C/85%RH testing is done per generic device/package family once a quarter.

C. E.S.D. and Latch-Up Testing

The RT70 die type has been found to have all pins able to withstand a transient pulse of $\pm 2000\text{V}$, per Mil-Std-883 Method 3015 (reference attached ESD Test Circuit). Latch-Up testing has shown that this device withstands a current of $\pm 250\text{mA}$.

Table 1
Reliability Evaluation Test Results

MAX3023EEExT

| TEST ITEM | TEST CONDITION | FAILURE IDENTIFICATION | PACKAGE | SAMPLE SIZE | NUMBER OF FAILURES |
|-----------------------------------|---|----------------------------------|-------------|-------------|--------------------|
| Static Life Test (Note 1) | | | | | |
| | Ta = 135°C Biased Time = 192 hrs. | DC Parameters & functionality | | 48 | 0 |
| Moisture Testing (Note 2) | | | | | |
| Pressure Pot | Ta = 121°C P = 15 psi. RH= 100% Time = 168hrs. | DC Parameters & functionality | QFN | 77 | 0 |
| | | | UCSP | 77 | 0 |
| 85/85 | Ta = 85°C RH = 85% Biased Time = 1000hrs. | DC Parameters & functionality | QFN UCSP | 77 N/A | 0 N/A |
| Mechanical Stress (Note 2) | | | | | |
| Temperature Cycle | -65°C/150°C 1000 Cycles Method 1010 (Note 3) | DC Parameters & functionality | QFN | 77 | 0 |
| | | | UCSP | 77 | 0 |

Note 1: Life Test Data may represent plastic DIP qualification lots.

Note 2: Generic Package/Process data

Note 3: UCSP Temperature Cycle performed at -40°C/125°C, 1000 Cycles, ramp rate 11°C/minute, dwell=15 minutes, One cycle/hour

Attachment #1

TABLE II. Pin combination to be tested. 1/ 2/

| | Terminal A (Each pin individually connected to terminal A with the other floating) | Terminal B (The common combination of all like-named pins connected to terminal B) |
|----|---|---|
| 1. | All pins except V_{PS1} 3/ | All V_{PS1} pins |
| 2. | All input and output pins | All other input-output pins |

1/ Table II is restated in narrative form in 3.4 below.

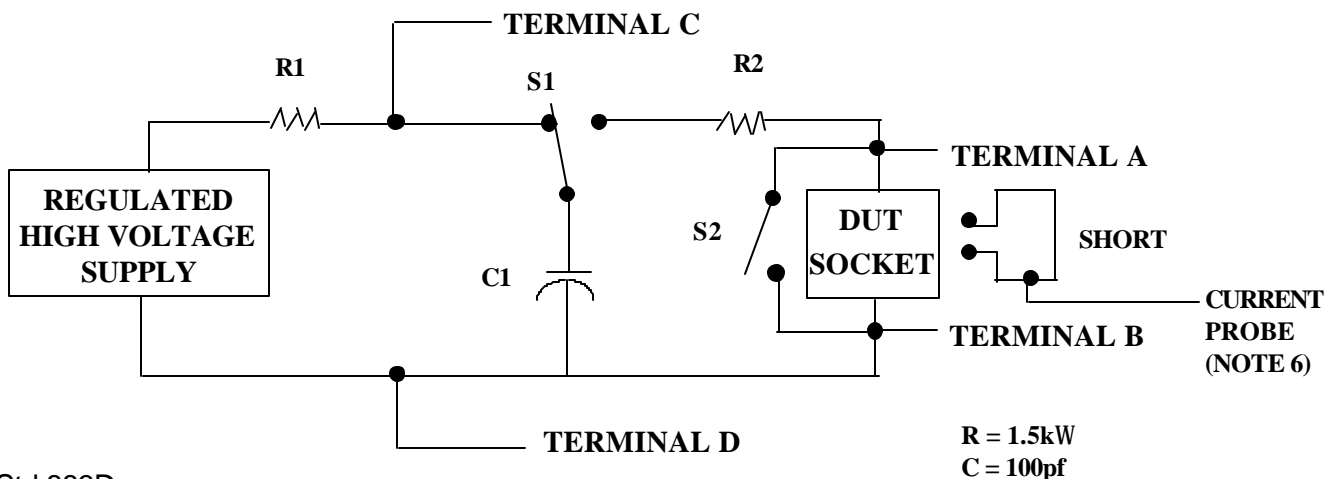
2/ No connects are not to be tested.

3/ Repeat pin combination I for each named Power supply and for ground

(e.g., where V_{PS1} is V_{DD} , V_{CC} , V_{SS} , V_{BB} , GND, $+V_S$, $-V_S$, V_{REF} , etc).

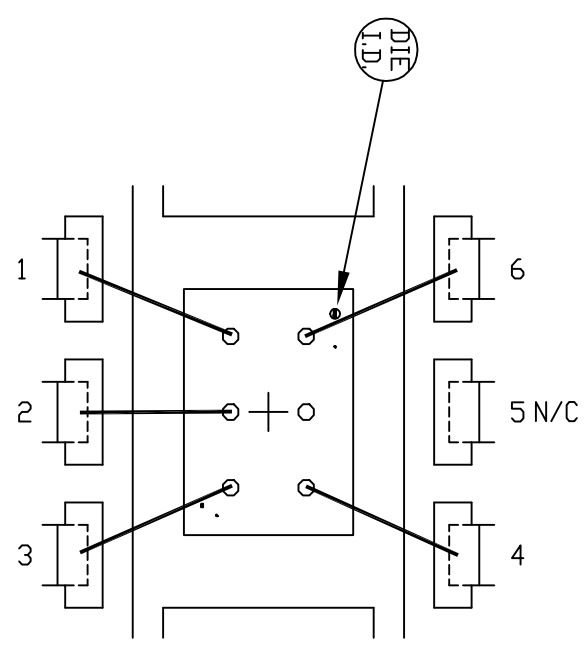
3.4 Pin combinations to be tested.

- Each pin individually connected to terminal A with respect to the device ground pin(s) connected to terminal B. All pins except the one being tested and the ground pin(s) shall be open.
- Each pin individually connected to terminal A with respect to each different set of a combination of all named power supply pins (e.g., V_{SS1} , or V_{SS2} or V_{SS3} or V_{CC1} , or V_{CC2}) connected to terminal B. All pins except the one being tested and the power supply pin or set of pins shall be open.
- Each input and each output individually connected to terminal A with respect to a combination of all the other input and output pins connected to terminal B. All pins except the input or output pin being tested and the combination of all the other input and output pins shall be open.



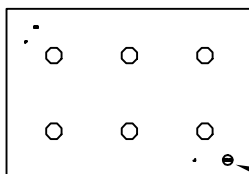
3x3x0.8 MM QFN THIN PKG.

EXPOSED PAD PKG.



| | | | | | |
|--------------------------|----------------|------------|------|---|-----------|
| PKG. CODE: T633-1 | | SIGNATURES | DATE |  CONFIDENTIAL & PROPRIETARY | |
| CAV./PAD SIZE: 71x102 | PKG. DESIGN | | | BOND DIAGRAM #: 05-9000-0264 | REV: A |

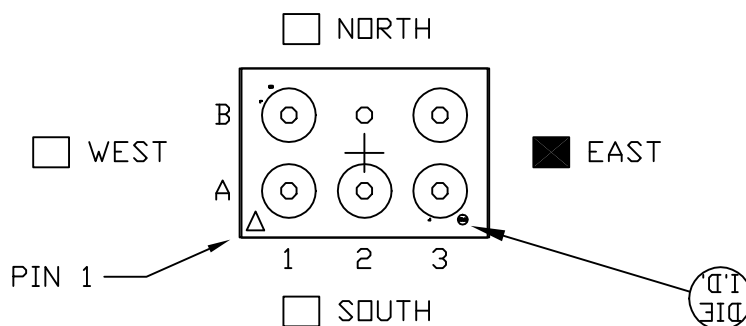
ORIGINAL CHIP



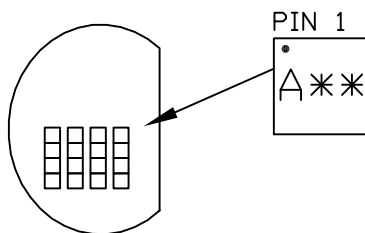
DIE
ID

*B2 BUMP IS DEPOPULATED

AFTER BUMP

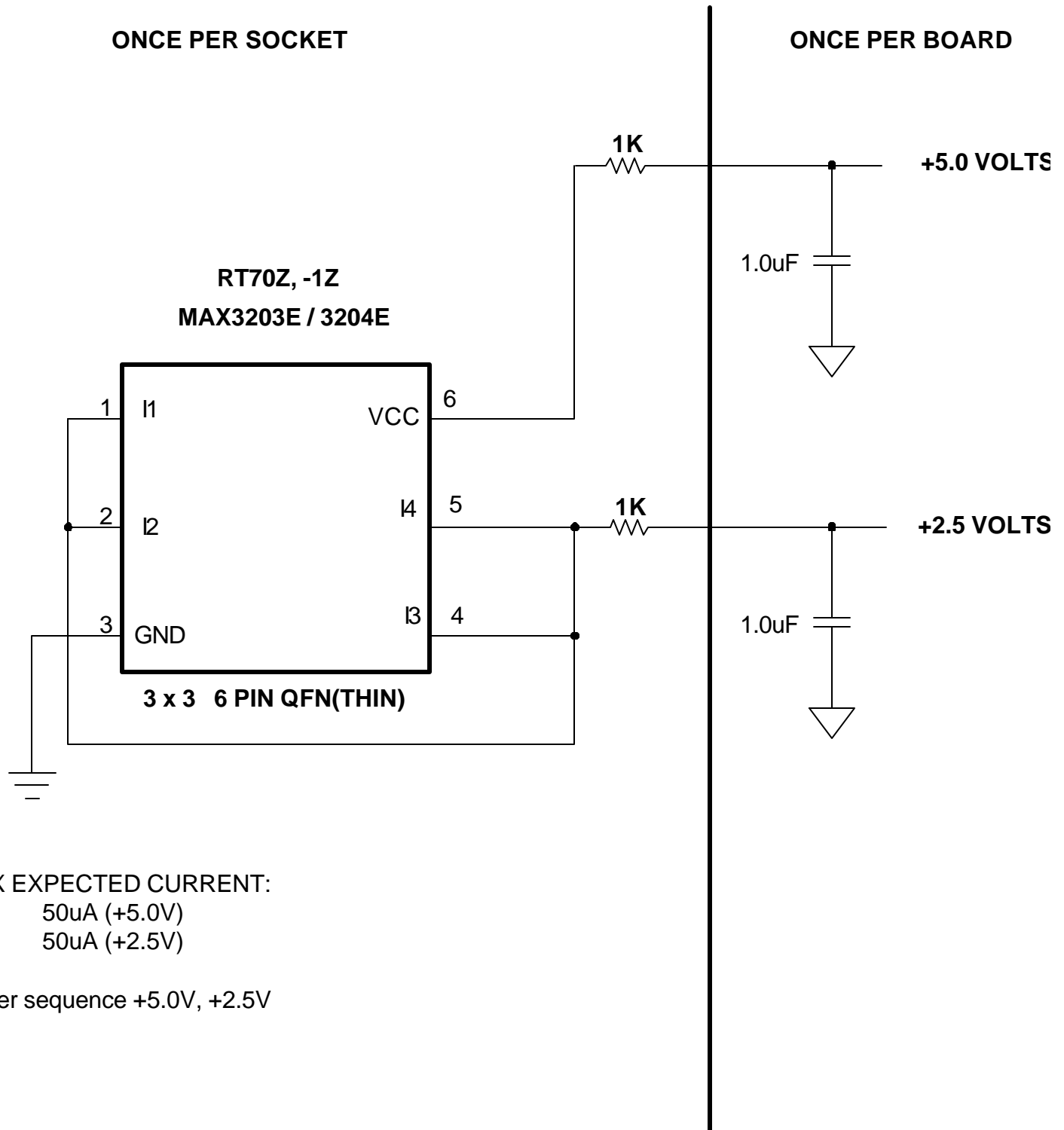


SELECT THE BOX INDICATING THE WAFER FLAT SIDE
WITH RESPECT TO PIN 1.



PART MARKING ORIENTATION
IN REFERENCE TO WAFER FLAT
(MARK IS ON WAFER BACKSIDE)

| | | | | | |
|-----------------------|----------------|------------|------|---|-----------|
| PKG. CODE: B6-4 | | SIGNATURES | DATE |  CONFIDENTIAL & PROPRIETARY | |
| CAV./PAD SIZE: N/A | PKG. DESIGN | | | BOND DIAGRAM #: 05-9000-0262 | REV: B |



MAX EXPECTED CURRENT:

50uA (+5.0V)

50uA (+2.5V)

Power sequence +5.0V, +2.5V